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TI: Transfer mold-type power semiconductor module for inverter, has power terminal connected to power circuit, that is bent twice so that it is initially separated from metal base and then extends along upward direction

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AB: NOVELTY - A power terminal (12) connected to power circuit, is bent twice such that it is initially separated from the metal base in the module, and then extends along upward direction. A control terminal (13) connected to control circuit section, is bent at right angle after it is extracted out from the module.; USE - Power semiconductor module such as insulated gate bipolar transistor module for electric power converters like inverter. ADVANTAGE - Provides power semiconductor module which is highly efficient and small in size. As the lead frame is effectively used and need for new control terminal is avoided, manufacturing cost is reduced. DESCRIPTION OF DRAWING(S) - The figure shows the sectional view of power semiconductor module. Power terminal 12 Control terminal 13

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